

# **BUK7219-55A**

# N-channel TrenchMOS standard level FET Rev. 02 — 3 February 2010

**Product data sheet** 

## **Product profile**

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

#### 1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. **Quick reference** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	55	V
$I_D$	drain current	$V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> and <u>3</u>	-	-	55	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	114	W
Avalanc	he ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 49 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 $\Omega$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	120	mJ
Static ch	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A;}$ $T_j = 175 \text{ °C;}$ see Figure 12 and 13	-	-	38	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12 and 13	-	16	19	mΩ



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	G	gate				
2	d	drain	mb	D		
3	S	source		$G \longrightarrow X$		
mb	D	mounting base; connected to drain		mbb076 S		
			SOT428 (DPAK)			

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7219-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	55	V
$V_{GS}$	gate-source voltage			-20	20	V
$I_D$	drain current	$T_{mb}$ = 100 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u>		-	39	Α
		T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; see <u>Figure 1</u> and <u>3</u>		-	55	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \mu s$ ; pulsed; see <u>Figure 3</u>	<u>[1]</u>	-	250	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	114	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 49 A; $V_{sup} \le$ 55 V; $R_{GS}$ = 50 $\Omega$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	120	mJ
Source-dr	ain diode					
Is	source current	T <sub>mb</sub> = 25 °C		-	55	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	250	Α

<sup>[1]</sup> Peak drain current is limited by chip, not package.

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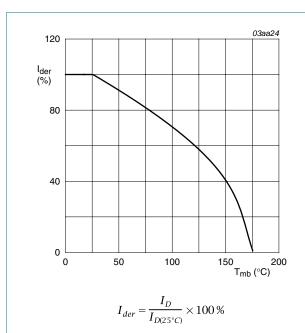


Fig 1. Normalized continuous drain current as a function of mounting base temperature

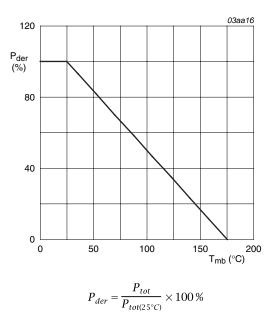
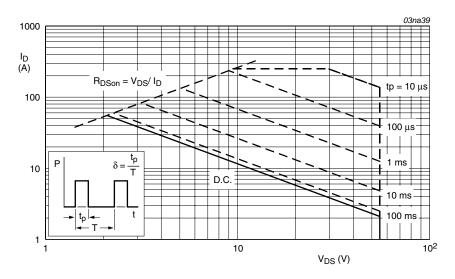


Fig 2. Normalized total power dissipation as a function of mounting base temperature



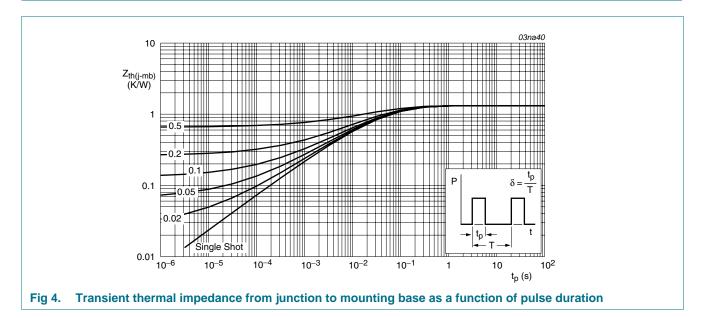
 $T_{amb} = 25$ °C;  $I_{DM}$  is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base		-	-	1.3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	see Figure 4	-	71.4	-	K/W



# 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
(DIT)DOO	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 11</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see <u>Figure 11</u>	-	-	4.4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see <u>Figure 11</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 175 °C; see Figure 12 and 13	-	-	38	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12 and 13	-	16	19	mΩ
Dynamic	characteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1581	2108	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	372	446	pF
C <sub>rss</sub>	reverse transfer capacitance		-	221	303	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	16	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$ ; $T_j = 25 °C$	-	70	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	57	-	ns
t <sub>f</sub>	fall time		-	41	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain lead from package to centre of die; $T_j = 25$ °C	-	2.5	-	nΗ
L <sub>S</sub>	internal source inductance	measured from source lead from package to source bond pad; T <sub>j</sub> = 25 °C	-	7.5	-	nΗ
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 14	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S$ = 25 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C	-	48	-	ns
Q <sub>r</sub>	recovered charge		-	106	_	nC

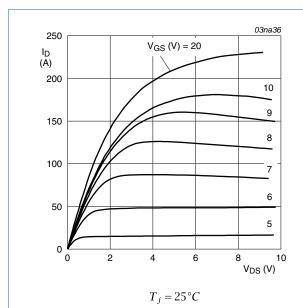


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

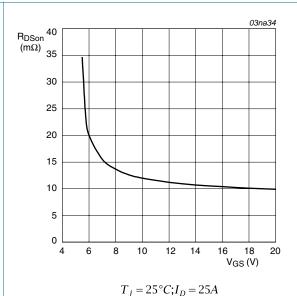
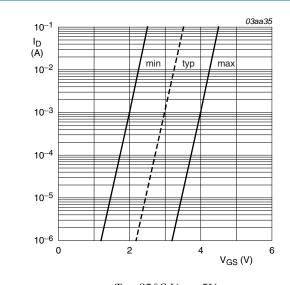
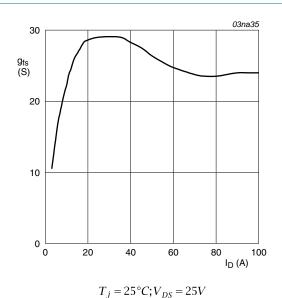


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_{j}=25~^{\circ}C; V_{DS}=5V$  Fig 7. Sub-threshold drain current as a function of

gate-source voltage



Forward transconductance as a



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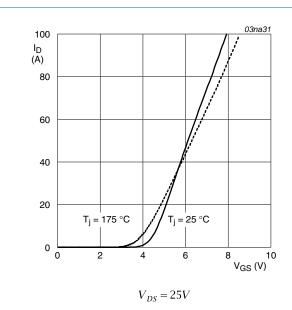


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

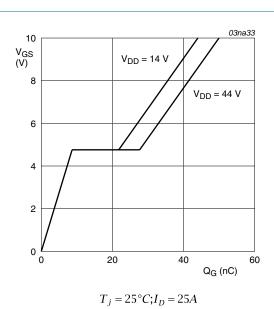


Fig 10. Gate-source voltage as a function of turn-on gate charge; typical values

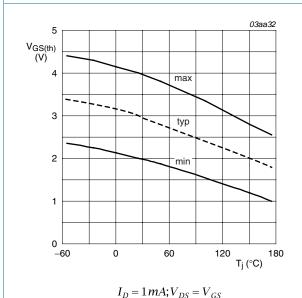


Fig 11. Gate-source threshold voltage as a function of junction temperature

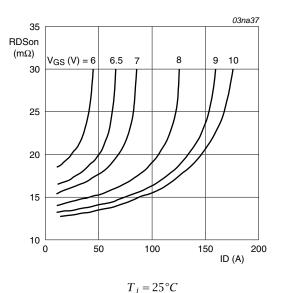


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

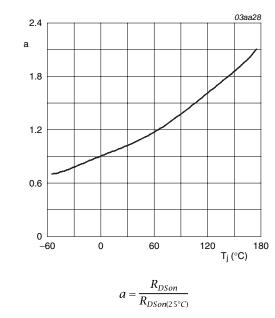


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

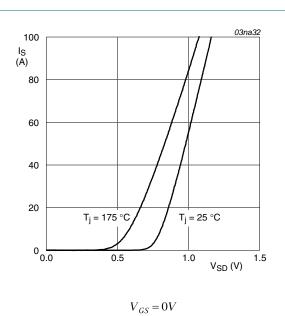


Fig 14. Reverse diode current as a function of reverse

diode voltage; typical values

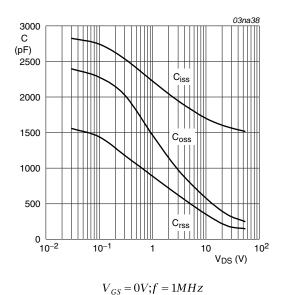


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

## 7. Package outline

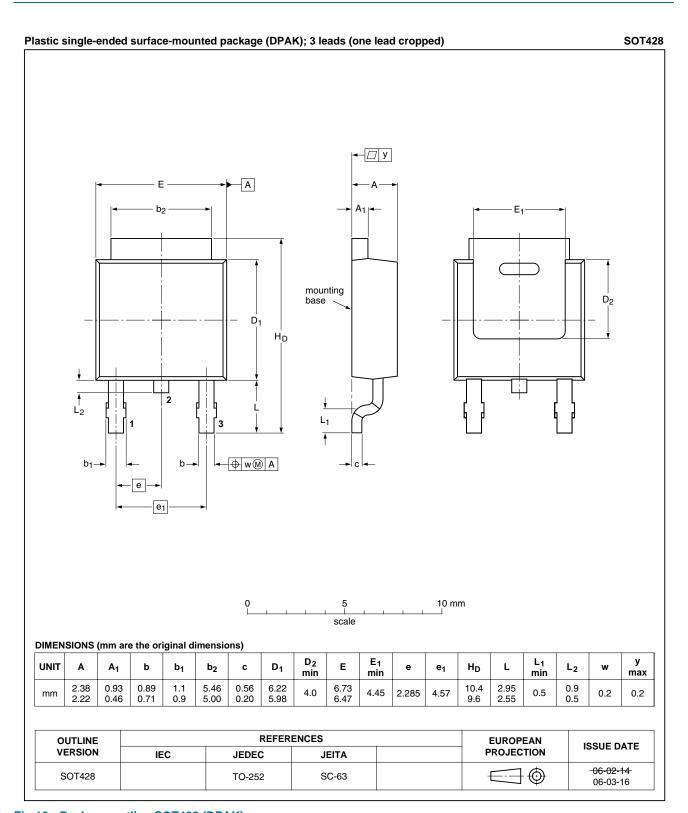


Fig 16. Package outline SOT428 (DPAK)

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# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BUK7219-55A_2	20100203	Product data sheet	-	BUK7219-55A-01	
Modifications:		The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.			
	<ul> <li>Legal texts</li> </ul>	have been adapted to the	new company name whe	re appropriate.	
BUK7219-55A-01 (9397 750 07575)	20001002	Product specification	-	-	

### 9. Legal information

#### 9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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